

PbSe near-infrared detector Multi-Pixel thin-film encapsulated

Features

- Bondable electrode for COB mounting
- High durability for rugged operation
- Suitable for automated wire-bonding
- Room temperature operation

Applications

- Spectroscopy
- Gas detection and analysis
- Flame monitoring
- Flame and spark detection
- Temperature measurement
- Moisture measurement

Electrical and optical characteristics per pixel

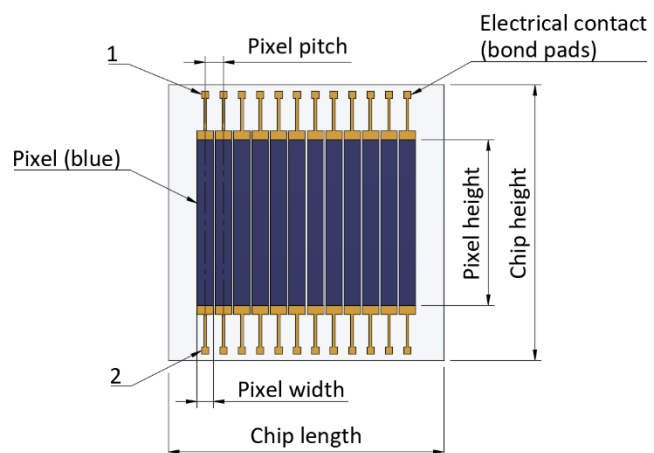
Element temperature [°C]	Peak wavelength λ_p [μm]	20% cut-off wavelength λ_c [μm]	Peak D^* (620 Hz, 1 Hz) [$\text{cm}\cdot\text{Hz}^{1/2}/\text{W}$]		Time constant [μs]	Dark resistance R_D [$\text{M}\Omega$]
	Typ.	Typ.	Typ.	Min.	Typ.	
22	3.8	4.5	$1.8 \cdot 10^{10}$	$1 \cdot 10^{10}$	4	0.3 - 20*

*depends on pixel geometry

- Measured with 500K blackbody
- Measured in a voltage divider circuit with 50 V/mm
- Photo responsivity and detectivity are measured with constant load resistance ($R_L = 1 \text{ M}\Omega$) and calculated for matched resistance

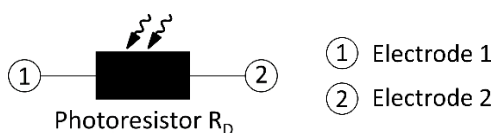
Possible mechanical characteristics

- Number of lines 1 - 4
- Number of pixels 2 - 16
- Minimum pixel width 20 μm
- Minimum pixel height 20 μm
- Minimum pixel pitch 50 μm
- Minimal chip length 3000 μm
- Minimal chip height 3000 μm



Please contact us for an individual design:
info@hertzstueck.de

Schematic



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trinamiX

A brand of
BASF – We create chemistry

Exemplary mechanical characteristics

Type No.	Number of lines	Number of pixels	Pixel pitch [μm]	Pixel width [μm]	Pixel height [μm]	Operating temperature [°C]
PbS_MP_01x12_0200_0180x1800	1	12	200	180	x 1800	-30 to +70

Die attach

- Use clean, soft rubber tip for pick and place handling
- UV-curing is not suitable due to permanent damage by UV light exposure
- Element temperature should never exceed +90°C

Wire-bonding

- Electrodes are optimized for room temperature Al-wire-bonding
- Element temperature should never exceed +90°C

Storage

- Storage temperature: -55°C to +90°C
- Exposure to UV light results in permanent damage
- Prevent exposure to UV and visible light

Handling

- Active area is scratch sensitive, protect top surface from any mechanical contact
 - Ensure dust-free environment for device handling
- Operating temperature: -30°C to +90°C

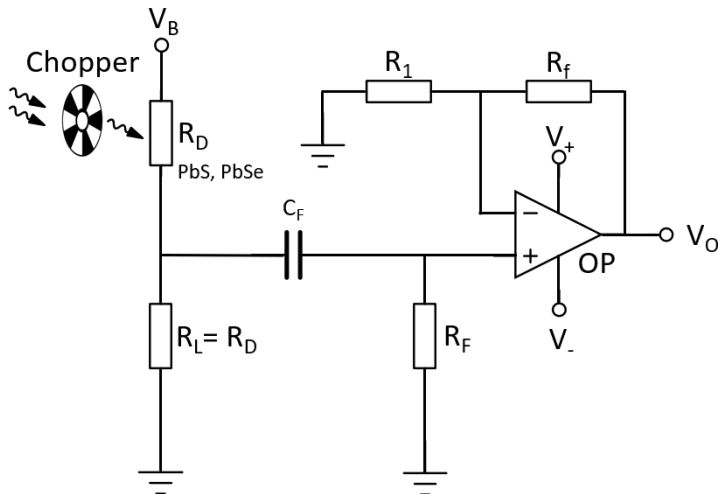
Options

- Individual housing
- Bonding onto PCB
- Integrated optics
- Evaluation-Kit available

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Exemplary circuit



- V_B : Bias voltage
- V_O : Output voltage
- R_D : Dark resistance of the detector
- R_L : Load resistor
- C_F : Filter capacitor
- R_F : Filter resistor
- R_f : Feedback resistor
- R_1 : Gain resistor

Regulatory

For the use of Hertzstück™ PbS and PbSe infrared photodetectors in medical devices, monitoring and control instruments and consumer applications RoHS exemptions apply.

For automotive applications Hertzstück™ PbS and PbSe infrared photodetectors fall under ELV exemption.